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Kind regards,

Team Nexperia

1PS76SB21; **BAT721** series

Schottky barrier diodes in small packages

Rev. 06 — 21 December 2006

Product data sheet

1. Product profile

1.1 General description

Planar Schottky barrier diodes with an integrated guard ring for stress protection. Encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		Configuration
	NXP	JEITA	
1PS76SB21	SOD323	SC-76	single
BAT721	SOT23	-	single
BAT721A	SOT23	-	dual common anode
BAT721C	SOT23	-	dual common cathode
BAT721S	SOT23	-	dual series

1.2 Features

- Low forward voltage
- Small SMD plastic packages
- Low capacitance

1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Line termination
- Reverse polarity protection

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
I _F	forward current		-	-	200	mA
V_R	reverse voltage		-	-	40	V
V_{F}	forward voltage	$I_F = 200 \text{ mA}$	<u>[1]</u> _	-	550	mV

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



2. Pinning information

Table 3. **Pinning** Pin Description Simplified outline **Symbol** 1PS76SB21 [1] 1 cathode 1 - 2 2 anode sym001 **BAT721** 1 anode 3 2 not connected 3 cathode n.c. 006aaa144 **BAT721A** cathode (diode 1) 3 2 cathode (diode 2) 3 anode (diode 1), anode (diode 2) 006aaa439 1 2 006aaa144 **BAT721C** 1 anode (diode 1) 3 2 anode (diode 2) 3 cathode (diode 1), cathode (diode 2) 006aaa438 2 006aaa144 **BAT721S** 1 anode (diode 1) 3 2 cathode (diode 2) 3 cathode (diode 1), anode (diode 2) 006aaa437 2 1 006aaa144

[1] The marking bar indicates the cathode.

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3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
1PS76SB21	SC-76	plastic surface-mounted package; 2 leads	SOD323			
BAT721	-	plastic surface-mounted package; 3 leads	SOT23			
BAT721A						
BAT721C						
BAT721S						

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
1PS76SB21	S1
BAT721	L7*
BAT721A	L8*
BAT721C	L9*
BAT721S	L0*

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V_R	reverse voltage		-	40	V
I _F	forward current		-	200	mA
I _{FSM}	non-repetitive peak forward current	half sine wave; JEDEC method; $t_p = 8.3 \text{ ms}$	-	1	Α
Tj	junction temperature		-	125	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

6. Thermal characteristics

Table 7. Thermal characteristics

Table 1.	Thermal Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diode							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>				
	1PS76SB21			-	-	450	K/W
	BAT721			-	-	500	K/W
	BAT721A			-	-	500	K/W
	BAT721C			-	-	500	K/W
	BAT721S			-	-	500	K/W

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

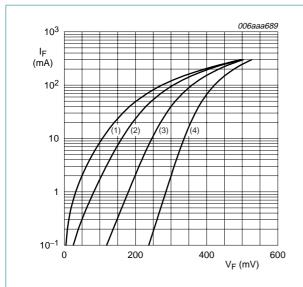
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

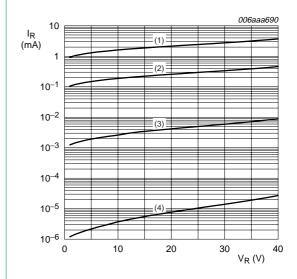
arrib		•				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	9					
V _F f	forward voltage	I _F = 10 mA	<u>[1]</u> _	-	300	mV
		I _F = 100 mA	<u>[1]</u> _	-	420	mV
		I _F = 200 mA	<u>[1]</u> _	-	550	mV
I _R	reverse current	$V_R = 30 \text{ V}$	-	-	15	μΑ
		$V_R = 30 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	-	3	mA
C _d	diode capacitance	$V_R = 0 V$; $f = 1 MHz$	-	40	50	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$



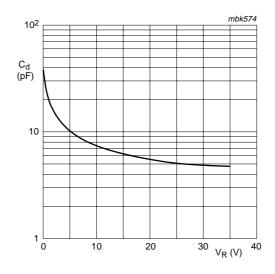
- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \,^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

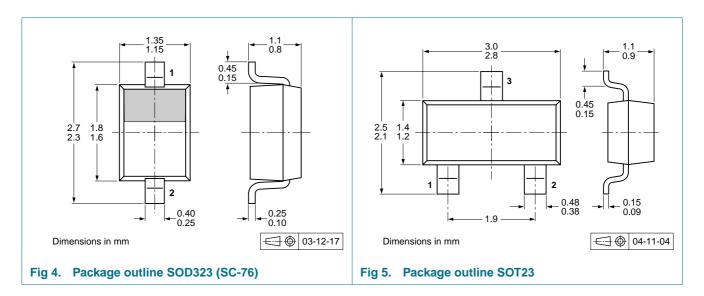
Fig 2. Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

Fig 3. Diode capacitance as a function of reverse voltage; typical values

8. Package outline



9. Packing information

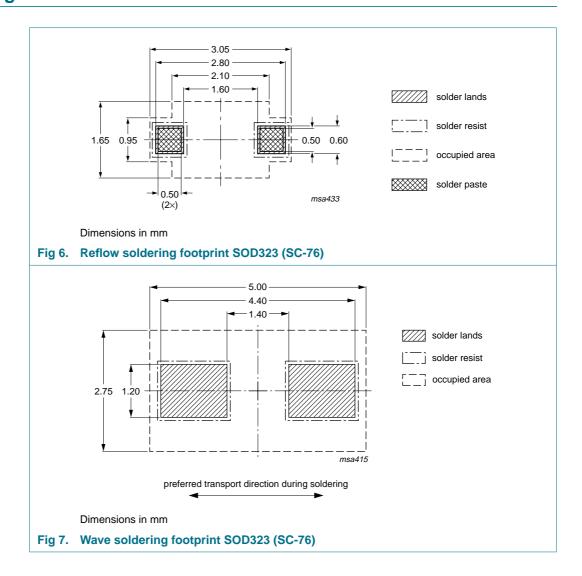
Table 9. Packing methods

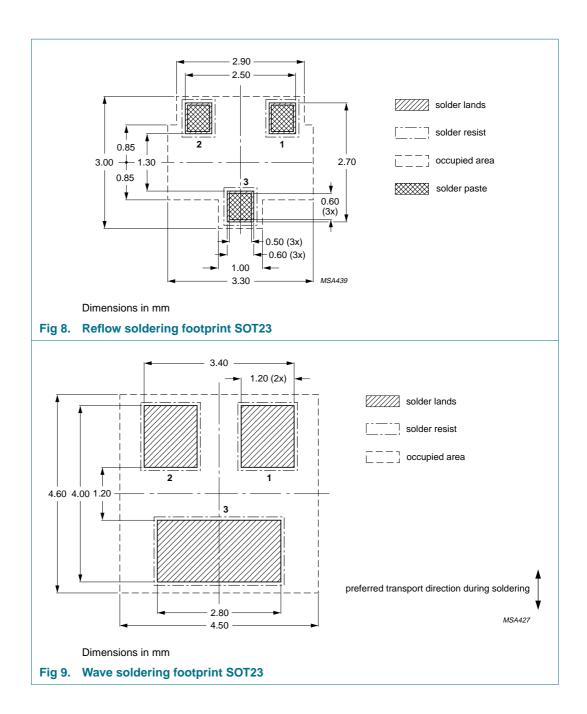
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity		
			3000	10000		
1PS76SB21	SOD323	4 mm pitch, 8 mm tape and reel	-115	-135		
BAT721	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
BAT721A						
BAT721C						
BAT721S						

[1] For further information and the availability of packing methods, see Section 13.

10. Soldering





11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
1PS76SB21_BAT721_SER_6	20061221	Product data sheet	-	1PS76SB21_BAT721 _SER_5				
Modifications:	 Amended Ta 	ble 10 "Revision history"						
1PS76SB21_BAT721_SER_5	20061205	Product data sheet	-	BAT721_SERIES_4 1PS76SB21_3				
Modifications:		of this data sheet has been in NXP Semiconductors.	redesigned to comply	with the new identity				
	 Legal texts h 	Legal texts have been adapted to the new company name where appropriate.						
	 This data she 1PS76SB21 	eet is a combination of data _3.	sheets BAT721_SER	IES_4 and				
	• Table 1 "Prod	duct overview": added						
	 Section 1.2 " 	Section 1.2 "Features": amended						
	 Section 1.3 " 	• Section 1.3 "Applications": amended						
	 Table 2 "Quid 	<u>Table 2 "Quick reference data"</u> : added						
	 Table 5 "Mar 	king codes": for 1PS76SB2	1 amended					
	 Table 5 "Mar 	king codes": enhanced table	e note section					
	• Table 6 "Limi	iting values": indication per	diode added					
	 Table 6 "Limiting 	iting values": for 1PS76SB2	1 I _{FSM} condition amen	ded				
	 Table 6 "Limiting 	iting values": T _{amb} ambient	emperature added					
	Table 7 "The	rmal characteristics": indica	tion per diode added					
	<u>Table 7</u>: R_{th(j}	-a) thermal resistance from j	unction to ambient co	ndition amended				
	 Table 8 "Cha 	racteristics": indication per	diode added					
	 Table 8 "Cha 	racteristics": reference to Ta	able note 1 amended					
		IPS76SB21 C _d minimum va	lue changed to typical	value				
	Figure 1 and	l 2: amended						
		15: superseded by minimize	d package outlines					
		acking information": added						
		Soldering": added						
	Section 12 "I	Legal information": updated						
BAT721_SERIES_4	20040315	Product specification	-	BAT721_SERIES_3				
1PS76SB21_3	20040126	Product specification	-	1PS76SB21_2				

1PS76SB21; BAT721 series

Schottky barrier diodes in small packages

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

1PS76SB21; BAT721 series

Schottky barrier diodes in small packages

14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	3
4	Marking	3
5	Limiting values	3
6	Thermal characteristics	4
7	Characteristics	4
8	Package outline	6
9	Packing information	6
10	Soldering	7
11	Revision history	9
12	Legal information 1	0
12.1	Data sheet status	10
12.2	Definitions	C
12.3	Disclaimers	0
12.4	Trademarks1	C
13	Contact information 1	0
14	Contents 1	11

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